

the same purpose may be substituted for the specific embodiment shown. This application is intended to cover any adaptations or variations of the present disclosure [invention]. Therefore, it is manifestly intended that embodiments of this invention be limited only by the claims and the equivalents thereof.

### IN THE CLAIMS

Please substitute the claim set in the appendix entitled "Clean Version of Pending Claims" for the previously pending claim set. The substitute claim set is intended to reflect cancellation of claims ~~13-15~~ and 25-31; the amendment of previously pending claims 1-3, 5-10, 16-17, 19-24, and 32-33; and the addition of new claims 36-45. The specific amendments to individual claims are detailed in the following marked-up set of claims.

1. (Amended) A substrate on which to mount an integrated circuit (IC) having a first dense formation of lands, the substrate comprising:  
a second dense formation of lands on a surface thereof formed in a geometrical pattern to maximize the density of the second dense formation of lands, while constrained by the size of individual lands and by the width and spacing of substrate traces coupled to the lands,  
wherein the second dense formation of lands is formed in a pattern comprising a combination of a face center rectangular pattern and a pattern from the group consisting of a zigzag pattern, a wave pattern, an undulating pattern, a vertical stack pattern, and any combination of a zigzag pattern, a wave pattern, an undulating pattern, and a vertical stack pattern.
2. (Amended) The substrate recited in claim 1, wherein the maximum trace escape density [of the second dense formation of lands] equals the reciprocal of  $(T_w + T_s)$ , and wherein  $T_w$  equals the width of the substrate traces and  $T_s$  equals the spacing between the substrate traces.
3. (Amended) The substrate recited in claim 1, wherein the second dense formation of lands is formed in a pattern comprising a combination of a face center rectangular pattern and a zigzag

pattern having [as] a plurality of zigzag rows.

5. (Amended) The substrate recited in claim 1, wherein the second dense formation of lands is formed in a pattern comprising a combination of a face center rectangular pattern and an undulating pattern [from the group consisting of a zigzag pattern, a wave pattern, an undulating pattern, a vertical stack pattern, and any combination of such patterns].
6. (Amended) The substrate recited in claim 1, wherein the second dense formation of lands is formed in a pattern comprising a combination of a face center rectangular pattern and a wave pattern [from the group consisting of a zigzag pattern, a wave pattern, an undulating pattern, a vertical stack pattern, and any combination of a zigzag pattern, a wave pattern, an undulating pattern, and a vertical stack pattern].
7. (Amended) An electronic package comprising:
  - an integrated circuit (IC) comprising a first plurality of lands on a surface thereof, including a first dense formation of lands;
  - a substrate comprising a second plurality of lands on a surface thereof, including a second dense formation of lands formed in an undulating [a geometrical] pattern to maximize the density of the second dense formation of lands, while constrained by the size of the second dense formation of lands and by the width and spacing of substrate traces coupled to the second dense formation of lands; and
  - elements coupling the first plurality of lands to the second plurality of lands.
8. (Amended) The electronic package recited in claim 7, wherein the maximum trace escape density [of the second dense formation of lands] equals the reciprocal of  $(Tw + Ts)$ , and wherein  $Tw$  equals the width of the substrate traces and  $Ts$  equals the spacing between the substrate traces.
9. (Amended) The electronic package recited in claim 7, wherein the second dense

formation of lands is formed as a plurality of undulating [zigzag] rows at the periphery of the surface of the substrate.

10. (Amended) The electronic package recited in claim 7, wherein the second dense formation of lands further comprises a face center rectangular pattern [is formed in a pattern from the group consisting of a zigzag pattern, a wave pattern, an undulating pattern, a vertical stack pattern, and any combination of such patterns].

16. (Amended) A data processing system comprising:  
a bus coupling components in the data processing system;  
a display coupled to the bus;  
external memory coupled to the bus; and  
a processor coupled to the bus and including at least one electronic package comprising:  
an integrated circuit (IC) comprising a first plurality of lands on a surface thereof,  
including a first dense formation of lands;  
a substrate comprising a second plurality of lands on a surface thereof, including a second dense formation of lands formed in an undulating [a geometrical] pattern to maximize the density of the second dense formation of lands, while constrained by the size of the second dense formation of lands and by the width and spacing of substrate traces coupled to the lands; and  
elements coupling the first plurality of lands to the second plurality of lands.

17. (Amended) The data processing system recited in claim 16, wherein the second dense formation of lands is formed as a plurality of undulating rows at the periphery of the surface of the substrate [in a pattern from the group consisting of a zigzag pattern, a wave pattern, an undulating pattern, a vertical stack pattern, and any combination of such patterns].

19. (Amended) A method comprising:  
forming on a substrate surface a plurality of traces, the traces having at least a predetermined width and a predetermined spacing from one another; and

forming within a die-bonding area on the substrate surface a plurality of lands, each coupled to a corresponding one of the plurality of traces, and each having at least a predetermined size, the plurality of traces escaping the die-bonding area, the plurality of lands being formed in at least one [a] geometrical pattern that maximizes the trace escape density [of such lands] while constrained by the land size and by the width and spacing of the traces, wherein the at least one geometrical pattern comprises a vertical stack pattern having at least three or more lands in a vertical stack.

20. (Amended) The method recited in claim 19, wherein the maximum trace escape density [of the plurality of lands] equals the reciprocal of  $(T_w + T_s)$ , and wherein  $T_w$  equals the width of the traces and  $T_s$  equals the spacing between the traces.
21. (Amended) The method recited in claim 19, wherein the plurality of lands are formed as a plurality of vertical stack patterns at the periphery of the surface of the substrate [zigzag rows].
22. (Amended) The method recited in claim 21, wherein the plurality of vertical stack patterns each comprise at least three lands, and wherein the substrate traces coupled to corresponding lands in each vertical stack are all located on the same side of the vertical stack [zigzag rows are substantially parallel].
23. (Amended) The method recited in claim 19, wherein the at least one geometrical pattern further comprises an undulating pattern [plurality of lands are formed in a pattern from the group consisting of a zigzag pattern, a wave pattern, an undulating pattern, a vertical stack pattern, and any combination of such patterns].
24. (Amended) The method recited in claim 19, wherein the at least one geometrical pattern further comprises a face center rectangular pattern [plurality of lands are formed in a pattern comprising a combination of a face center rectangular pattern and a pattern from the group consisting of a zigzag pattern, a wave pattern, an undulating pattern, a vertical stack pattern, and

any combination of a zigzag pattern, a wave pattern, an undulating pattern, and a vertical stack pattern].

32. (Amended) A method comprising:

forming lands within a die-bonding area on a substrate surface in a geometrical pattern to maximize the trace escape density of traces coupled to the lands and escaping the die-bonding area on the substrate surface [such lands] while constrained by the land size and by the width and spacing of the traces [coupled to the lands and formed on the substrate surface], wherein the lands are formed in a vertical stack pattern having at least three or more lands in a vertical stack; and

coupling lands on an integrated circuit (IC) to corresponding lands on the substrate surface.

33. (Amended) The method recited in claim 32, wherein the maximum trace escape density [of the plurality of lands] equals the reciprocal of  $(Tw + Ts)$ , and wherein  $Tw$  equals the width of the traces and  $Ts$  equals the spacing between the traces.

Please add new claims 36-45 as follows:

36. (New) A substrate having a die-bonding area on which to mount an integrated circuit (IC) having a first dense formation of lands, the substrate comprising:

a second dense formation of lands on a surface thereof, each land having coupled thereto a substrate trace escaping the die-bonding area;

wherein the second dense formation of lands is formed in an undulating pattern.

37. (New) The substrate recited in claim 36, wherein the maximum trace escape density equals the reciprocal of  $(Tw + Ts)$ , and wherein  $Tw$  equals the width of the substrate traces and  $Ts$  equals the spacing between the substrate traces.

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38. (New) The substrate recited in claim 36, wherein the second dense formation of lands comprises a plurality of undulating rows at the periphery of the surface of the substrate.
39. (New) The substrate recited in claim 36, wherein the second dense formation of lands further comprises a face center rectangular pattern.
40. (New) A substrate having a die-bonding area on which to mount an integrated circuit (IC) having a first dense formation of lands, the substrate comprising:  
a second dense formation of lands on a surface thereof, each land having coupled thereto a corresponding substrate trace escaping the die-bonding area;  
wherein the second dense formation of lands is formed in a vertical stack pattern having at least one group of three or more lands in a vertical stack; and  
wherein the substrate traces coupled to corresponding lands in a vertical stack are all located on the same side of the vertical stack.
41. (New) The substrate recited in claim 40, wherein the maximum trace escape density equals the reciprocal of  $(T_w + T_s)$ , and wherein  $T_w$  equals the width of the substrate traces and  $T_s$  equals the spacing between the substrate traces.
42. (New) The substrate recited in claim 40, wherein the second dense formation of lands comprises a plurality of vertical stacks at the periphery of the surface of the substrate.
43. (New) The substrate recited in claim 40, wherein the second dense formation of lands further comprises a face center rectangular pattern.
44. (New) The method recited in claim 32, wherein the lands are formed as a plurality of vertical stack patterns at the periphery of the surface of the substrate.